

FEATURES

- High reliability LPE GaAlAs IRLEDs
- Ultra high power output
- 880nm peak emission
- Six chips connected in series
- Very wide angle of emission
- Electrically isolated case

All surfaces are gold plated. Dimensions are nominal values in inches unless otherwise specified.



ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P _o	I _F = 300mA I _F = 6A	300	330 5000		mW
Peak Emission Wavelength, λ _p	I _F = 50mA		880		nm
Spectral Bandwidth at 50%, Δλ			80		nm
Half Intensity Beam Angle, θ				120	
Forward Voltage, V _F	I _F = 300mA		9	10	Volts
Reverse Breakdown Voltage, V _R	I _R = 10μA	5	30		Volts
Capacitance, C	V _R = 0V		15		pF
Rise Time			2		μsec
Fall Time			2		μsec

ABSOLUTE MAXIMUM RATINGS AT 25°C CASE

Power Dissipation ¹	4W
Continuous Forward Current	400mA
Peak Forward Current (10μs, 400Hz) ²	6A
Reverse Voltage	5V
Lead Soldering Temperature (1/16" from case for 10sec)	260°C

¹Derate per Thermal Derating Curve above 25°C

²Derate linearly above 25°C

THERMAL PARAMETERS

Storage and Operating Temperature Range	-55°C to 100°C
Maximum Junction Temperature	100°C
Thermal Resistance, R _{THJA} ¹	60°C/W Typical
Thermal Resistance, R _{THJA} ²	16°C/W Typical

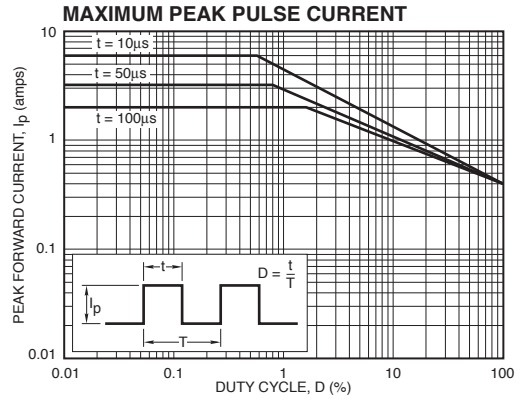
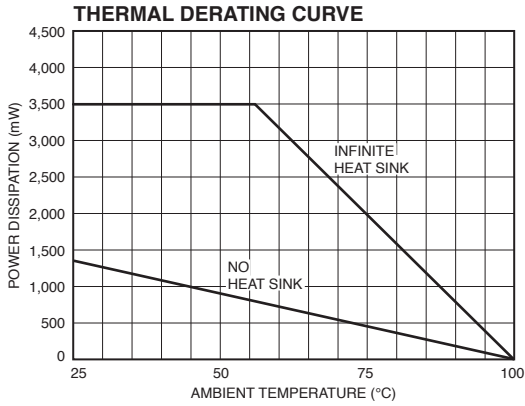
¹Heat transfer minimized by measuring in still air with minimum heat conducting through leads

²Air circulating at a rapid rate to keep case temperature at 25°C



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MAXIMUM RATINGS



TYPICAL CHARACTERISTICS

